

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC74VCX162843FT

Low-Voltage 18-Bit D-Type Latch with 3.6-V Tolerant Inputs and Outputs

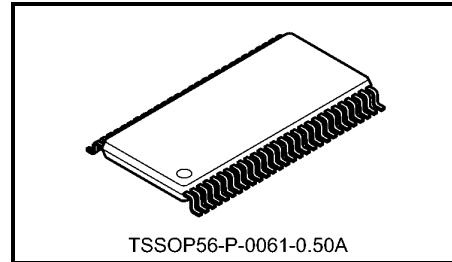
The TC74VCX162843FT is a high-performance CMOS 18-bit D-type latch. Designed for use in 1.8-V, 2.5-V or 3.3-V systems, it achieves high-speed operation while maintaining the CMOS low power dissipation.

It is also designed with overvoltage tolerant inputs and outputs up to 3.6 V.

The TC74VCX162843FT can be used as two 9-bit latches or one 18-bit latch. The 18 latches are transparent D-type latches. The device has noninverting data (D) inputs and provides true data at its outputs. While the latch-enable (1LE or 2LE) input is high, the Q outputs of the corresponding 9-bit latch follow the D inputs. When LE is taken low, the Q outputs are latched at the levels set up at the D inputs. \overline{CLR} and \overline{PR} are independent of the CK and are accomplished by setting the appropriate input low. When the \overline{OE} input is high, the outputs are in a high-impedance state. This device is designed to be used with 3-state memory address drivers, etc.

The $26\text{-}\Omega$ series resistor helps reducing output overshoot and undershoot without external resistor.

All inputs are equipped with protection circuits against static discharge.

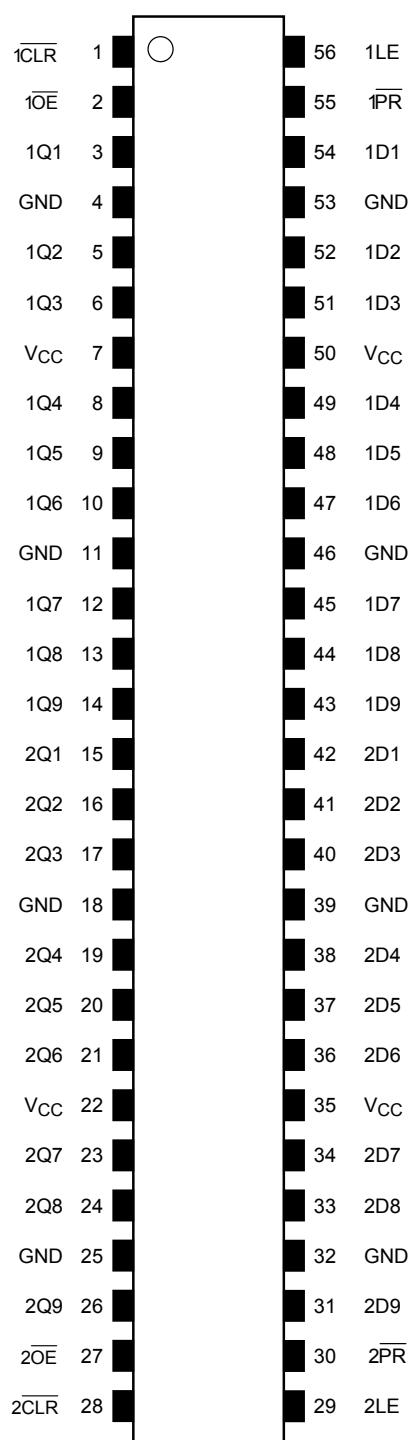


Weight: 0.25 g (typ.)

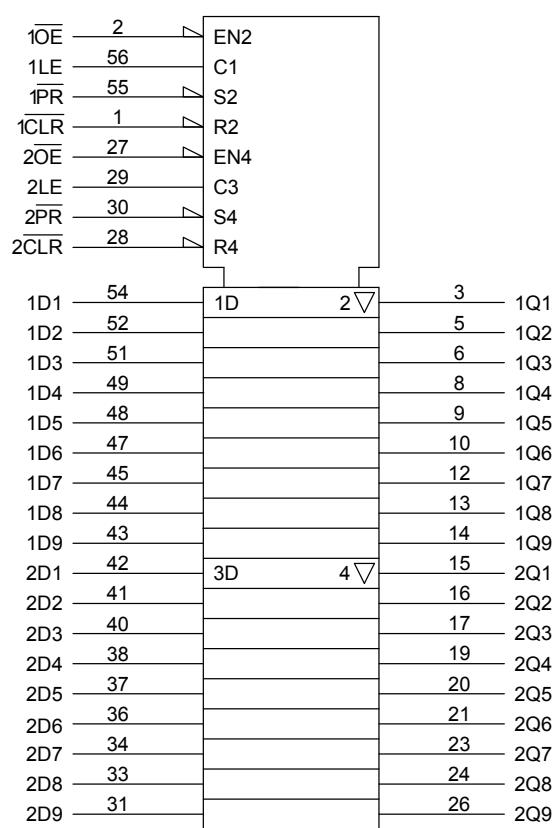
Features

- 26- Ω series resistors on outputs
- Low-voltage operation: $V_{CC} = 1.8$ to 3.6 V
- High-speed operation: $t_{pd} = 3.9$ ns (max) ($V_{CC} = 3.0$ to 3.6 V)
 - : $t_{pd} = 5.1$ ns (max) ($V_{CC} = 2.3$ to 2.7 V)
 - : $t_{pd} = 9.8$ ns (max) ($V_{CC} = 1.8$ V)
- Output current: $I_{OH}/I_{OL} = \pm 12$ mA (min) ($V_{CC} = 3.0$ V)
 - : $I_{OH}/I_{OL} = \pm 8$ mA (min) ($V_{CC} = 2.3$ V)
 - : $I_{OH}/I_{OL} = \pm 4$ mA (min) ($V_{CC} = 1.8$ V)
- Latch-up performance: -300 mA
- ESD performance: Machine model $\geq \pm 200$ V
Human body model $\geq \pm 2000$ V
- Package: TSSOP
- 3.6-V tolerant function and power-down protection provided on all inputs and outputs

Pin Assignment (top view)



IEC Logic Symbol



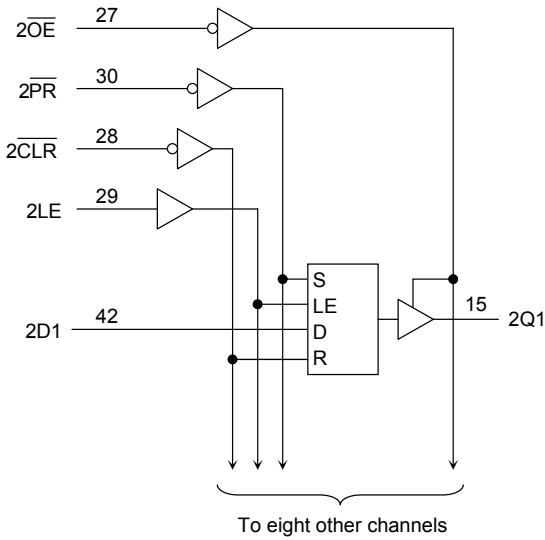
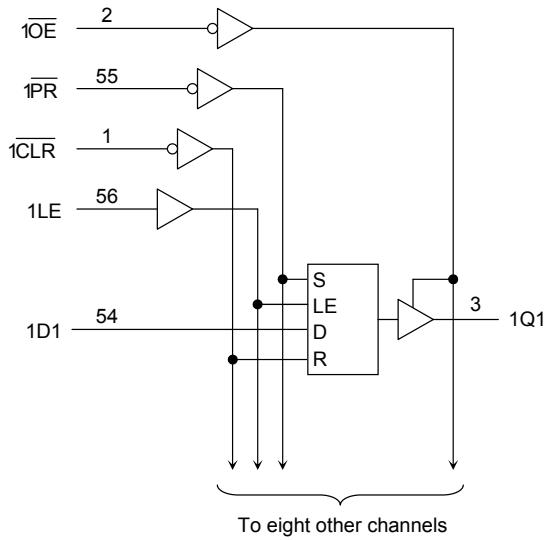
Truth Table (each 9-bit latch)

Inputs					Outputs
\overline{PR}	\overline{CLR}	\overline{OE}	LE	D	Q
L	X	L	X	X	H
H	L	L	X	X	L
H	H	L	H	L	L
H	H	L	H	H	H
H	H	L	L	X	Qn
X	X	H	X	X	Z

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE input is taken to a low logic level.

System Diagram

Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	-0.5 to 4.6	V
DC input voltage	V _{IN}	-0.5 to 4.6	V
DC output voltage	V _{OUT}	-0.5 to 4.6 (Note 2)	V
		-0.5 to V _{CC} + 0.5 (Note 3)	
Input diode current	I _{IK}	-50	mA
Output diode current	I _{OK}	±50 (Note 4)	mA
DC output current	I _{OUT}	±50	mA
Power dissipation	P _D	400	mW
DC V _{CC} /ground current per supply pin	I _{CC} /I _{GND}	±100	mA
Storage temperature	T _{stg}	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc.).

Note 2: OFF state

Note 3: High or low state. I_{OUT} absolute maximum rating must be observed.

Note 4: V_{OUT} < GND, V_{OUT} > V_{CC}

Operating Ranges (Note 1)

Characteristics	Symbol	Rating	Unit
Power supply voltage	V _{CC}	1.8 to 3.6	V
		1.2 to 3.6 (Note 2)	
Input voltage	V _{IN}	-0.3 to 3.6	V
Output voltage	V _{OUT}	0 to 3.6 (Note 3)	V
		0 to V _{CC} (Note 4)	
Output current	I _{OH} /I _{OL}	±12 (Note 5)	mA
		±8 (Note 6)	
		±4 (Note 7)	
Operating temperature	T _{opr}	-40 to 85	°C
Input rise and fall time	dt/dv	0 to 10 (Note 8)	ns/V

Note 1: The operating ranges must be maintained to ensure the normal operation of the device.
Unused inputs must be tied to either V_{CC} or GND.

Note 2: Data retention only

Note 3: OFF state

Note 4: High or low state

Note 5: V_{CC} = 3.0 to 3.6 V

Note 6: V_{CC} = 2.3 to 2.7 V

Note 7: V_{CC} = 1.8 V

Note 8: V_{IN} = 0.8 to 2.0 V, V_{CC} = 3.0 V

Electrical Characteristics**DC Characteristics ($T_a = -40$ to 85°C , $2.7 \text{ V} < V_{CC} \leq 3.6 \text{ V}$)**

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	H-level	V_{IH}	—			2.7 to 3.6	2.0	—	
	L-level	V_{IL}	—			2.7 to 3.6	—	0.8	
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	2.7 to 3.6	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -6 \text{ mA}$	2.7	2.2	—		
				$I_{OH} = -8 \text{ mA}$	3.0	2.4	—		
				$I_{OH} = -12 \text{ mA}$	3.0	2.2	—		
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	2.7 to 3.6	—	0.2	V	
				$I_{OL} = 6 \text{ mA}$	2.7	—	0.4		
				$I_{OL} = 8 \text{ mA}$	3.0	—	0.55		
				$I_{OL} = 12 \text{ mA}$	3.0	—	0.8		
Input leakage current	I_{IN}	$V_{IN} = 0$ to 3.6 V		2.7 to 3.6		—	± 5.0	μA	
3-state output OFF state current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		2.7 to 3.6		—	± 10.0	μA	
Power-off leakage current	I_{OFF}	$V_{IN}, V_{OUT} = 0$ to 3.6 V		0		—	10.0	μA	
Quiescent supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.7 to 3.6		—	20.0	μA	
		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		2.7 to 3.6		—	± 20.0		
Increase in I_{CC} per input	ΔI_{CC}	$V_{IH} = V_{CC} - 0.6 \text{ V}$		2.7 to 3.6		—	750		

DC Characteristics ($T_a = -40$ to 85°C , $2.3 \text{ V} \leq V_{CC} \leq 2.7 \text{ V}$)

Characteristics		Symbol	Test Condition		$V_{CC} (\text{V})$	Min	Max	Unit	
Input voltage	H-level	V_{IH}	—			2.3 to 2.7	1.6	—	
	L-level	V_{IL}	—			2.3 to 2.7	—	0.7	
Output voltage	H-level	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$	2.3 to 2.7	$V_{CC} - 0.2$	—	V	
				$I_{OH} = -4 \text{ mA}$	2.3	2.0	—		
				$I_{OH} = -6 \text{ mA}$	2.3	1.8	—		
				$I_{OH} = -8 \text{ mA}$	2.3	1.7	—		
	L-level	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$	2.3 to 2.7	—	0.2	V	
				$I_{OL} = 6 \text{ mA}$	2.3	—	0.4		
				$I_{OL} = 8 \text{ mA}$	2.3	—	0.6		
				$I_{OL} = 12 \text{ mA}$	2.3	—	0.8		
Input leakage current	I_{IN}	$V_{IN} = 0$ to 3.6 V		2.3 to 2.7		—	± 5.0	μA	
3-state output OFF state current	I_{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V		2.3 to 2.7		—	± 10.0	μA	
Power-off leakage current	I_{OFF}	$V_{IN}, V_{OUT} = 0$ to 3.6 V		0		—	10.0	μA	
Quiescent supply current	I_{CC}	$V_{IN} = V_{CC}$ or GND		2.3 to 2.7		—	20.0	μA	
		$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		2.3 to 2.7		—	± 20.0		

DC Characteristics ($T_a = -40$ to 85°C , $1.8 \leq V_{CC} < 2.3$ V)

Characteristics		Symbol	Test Circuit	Test Condition		V_{CC} (V)	Min	Max	Unit		
Input voltage	H-level	V_{IH}	—	—			1.8 to 2.3	$0.7 \times V_{CC}$	—	V	
	L-level	V_{IL}	—	—			1.8 to 2.3	—	$0.2 \times V_{CC}$		
Output voltage	H-level	V_{OH}	—	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OH} = -100 \mu\text{A}$ $I_{OH} = -4 \text{ mA}$	1.8	$V_{CC} - 0.2$	—	V		
	L-level	V_{OL}	—	$V_{IN} = V_{IH}$ or V_{IL}	$I_{OL} = 100 \mu\text{A}$ $I_{OL} = 4 \text{ mA}$	1.8	—	0.2			
Input leakage current	I_{IN}	—	$V_{IN} = 0$ to 3.6 V			1.8	—	± 5.0	μA		
3-state output OFF state current	I_{OZ}	—	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = 0$ to 3.6 V			1.8	—	± 10.0	μA		
Power-off leakage current	I_{OFF}	—	$V_{IN}, V_{OUT} = 0$ to 3.6 V			0	—	10.0	μA		
Quiescent supply current	I_{CC}	—	$V_{IN} = V_{CC}$ or GND			1.8	—	20.0	μA		
		—	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6$ V			1.8	—	± 20.0			

AC Characteristics (Ta = -40 to 85°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω) (Note 1)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Min	Max	Unit
Propagation delay time (D-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.1	
			3.3 ± 0.3	0.6	3.9	
Propagation delay time (LE-Q)	t _{pLH} t _{pHL}	Figure 1, Figure 2	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.8	
			3.3 ± 0.3	0.6	4.4	
Propagation delay time (PR -Q)	t _{pLH}	Figure 1, Figure 3	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	7.0	
			3.3 ± 0.3	0.6	4.9	
Propagation delay time (CLR -Q)	t _{pHL}	Figure 1, Figure 3	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	6.0	
			3.3 ± 0.3	0.6	4.6	
3-state output enable time	t _{pZL} t _{pZH}	Figure 1, Figure 4	1.8	1.5	9.8	ns
			2.5 ± 0.2	0.8	5.9	
			3.3 ± 0.3	0.6	4.3	
3-state output disable time	t _{pLZ} t _{pHZ}	Figure 1, Figure 4	1.8	1.5	8.8	ns
			2.5 ± 0.2	0.8	4.9	
			3.3 ± 0.3	0.6	4.3	
Minimum pulse width (LE, PR , CLR)	t _W (H) t _W (L)	Figure 1, Figure 2, Figure 3	1.8	4.0	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum setup time	t _s	Figure 1, Figure 2	1.8	2.5	—	ns
			2.5 ± 0.2	1.5	—	
			3.3 ± 0.3	1.5	—	
Minimum hold time	t _h	Figure 1, Figure 2	1.8	1.0	—	ns
			2.5 ± 0.2	1.0	—	
			3.3 ± 0.3	1.0	—	
Minimum removal time	t _{rem}	Figure 1, Figure 5	1.8	4.0	—	ns
			2.5 ± 0.2	3.0	—	
			3.3 ± 0.3	2.0	—	
Output to output skew	t _{osLH} t _{osHL}	(Note 2)	1.8	—	0.5	ns
			2.5 ± 0.2	—	0.5	
			3.3 ± 0.3	—	0.5	

Note 1: For C_L = 50 pF, add approximately 300 ps to the AC maximum specification.

Note 2: Parameter guaranteed by design.

$$(t_{osLH} = |t_{pLHm} - t_{pLHn}|, t_{osHL} = |t_{pHLm} - t_{pHLn}|)$$

Dynamic Switching Characteristics(Ta = 25°C, input: t_r = t_f = 2.0 ns, C_L = 30 pF, R_L = 500 Ω)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Quiet output maximum dynamic V _{OL}	V _{OLP}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	0.35	
Quiet output minimum dynamic V _{OL}	V _{OLV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	-0.15	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	-0.25	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	-0.35	
Quiet output minimum dynamic V _{OH}	V _{OHV}	V _{IH} = 1.8 V, V _{IL} = 0 V (Note)	1.8	1.55	V
		V _{IH} = 2.5 V, V _{IL} = 0 V (Note)	2.5	2.05	
		V _{IH} = 3.3 V, V _{IL} = 0 V (Note)	3.3	2.65	

Note: Parameter guaranteed by design.

Capacitive Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	V _{CC} (V)	Typ.	Unit
Input capacitance	C _{IN}	—	1.8, 2.5, 3.3	6	pF
Output capacitance	C _O	—	1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C _{PD}	f _{IN} = 10 MHz (Note)	1.8, 2.5, 3.3	20	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

$$I_{CC\text{ (opr)}} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/18 \text{ (per bit)}$$

AC Test Circuit

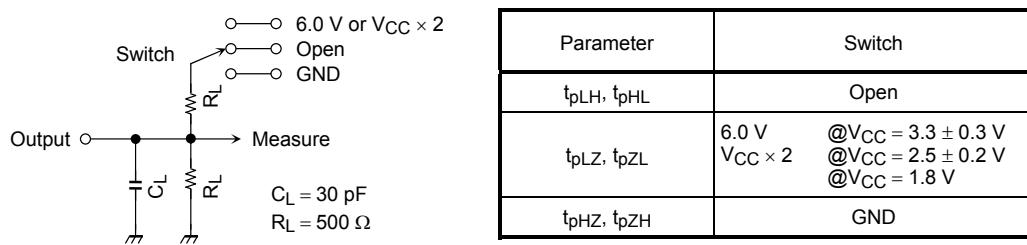
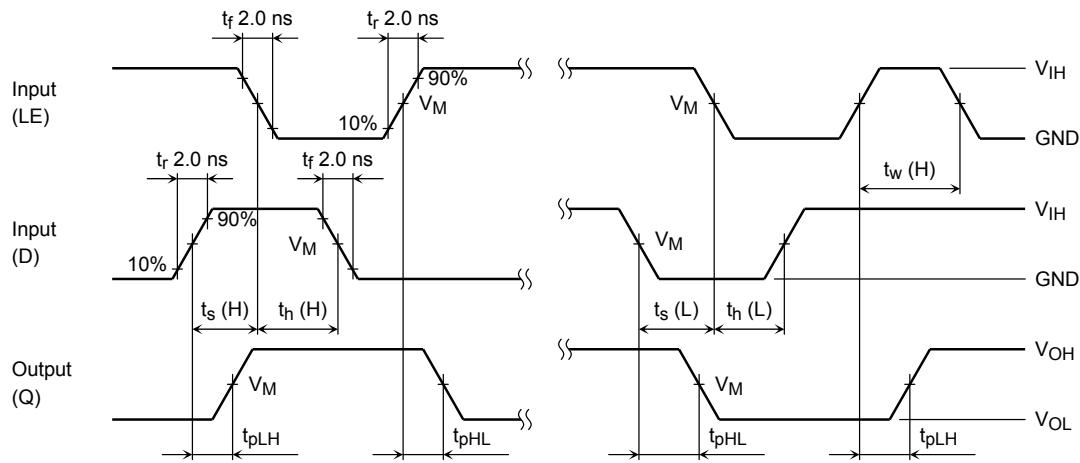
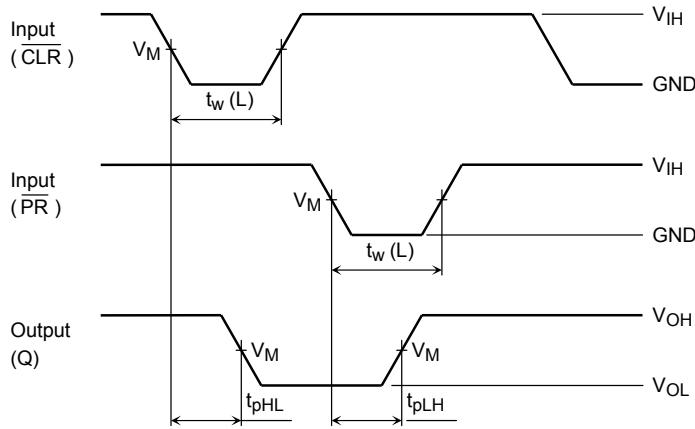
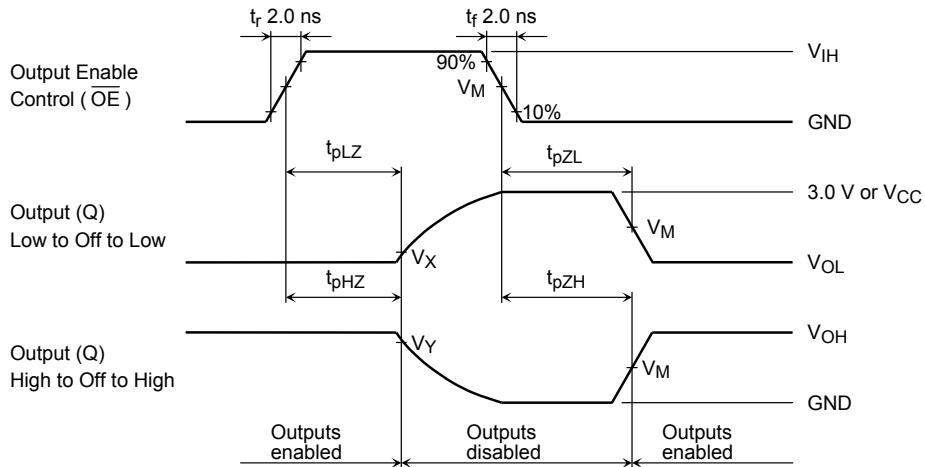
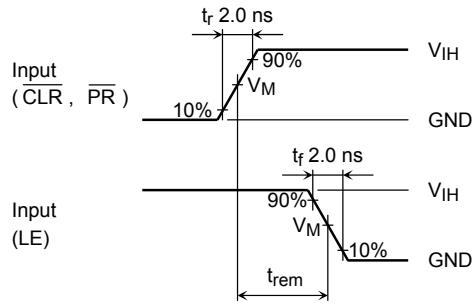


Figure 1

AC Waveform

Figure 2 $t_{pLH}, t_{pHL}, t_w, t_s, t_h$ Figure 3 t_{pLH}, t_{pHL}, t_w

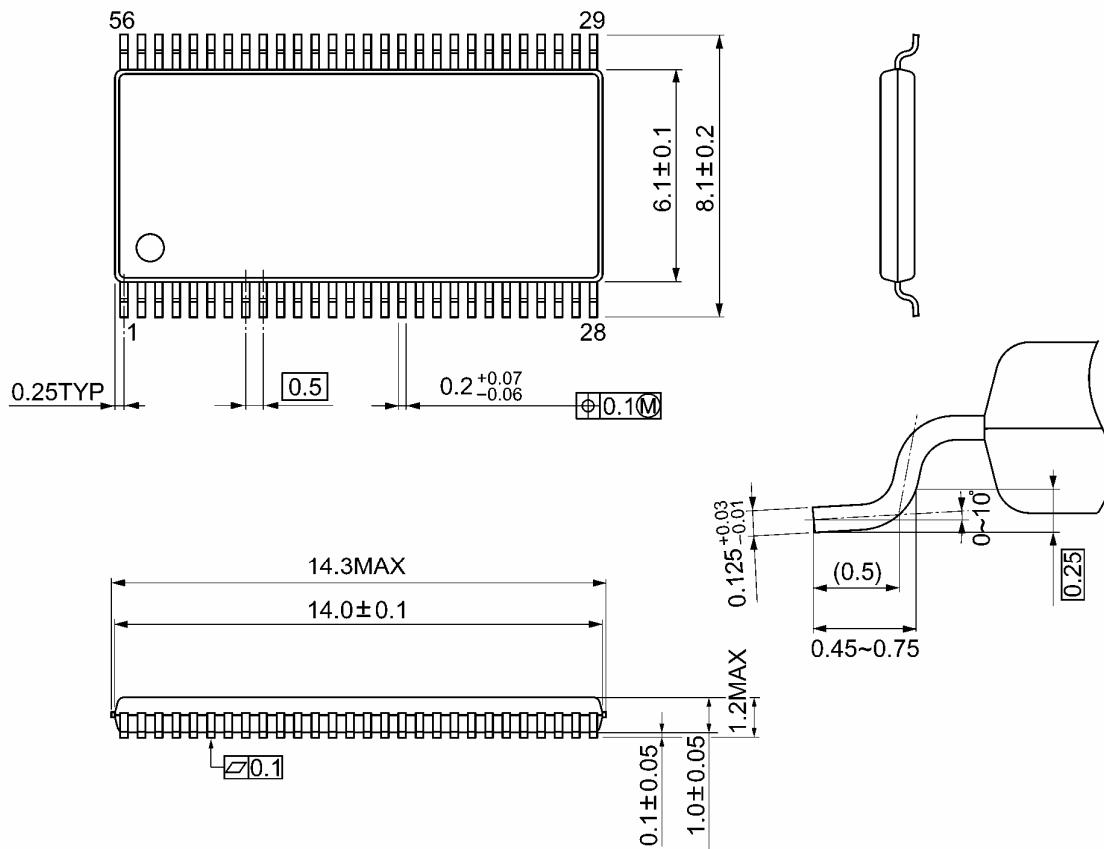
Figure 4 t_{pLZ} , t_{pHZ} , t_{pZL} , t_{pZH} Figure 5 t_{rem}

Symbol	V_{CC}		
	3.3 ± 0.3 V	2.5 ± 0.2 V	1.8 V
V_{IH}	2.7 V	V_{CC}	V_{CC}
V_M	1.5 V	$V_{CC}/2$	$V_{CC}/2$
V_X	$V_{OL} + 0.3$ V	$V_{OL} + 0.15$ V	$V_{OL} + 0.15$ V
V_Y	$V_{OH} - 0.3$ V	$V_{OH} - 0.15$ V	$V_{OH} - 0.15$ V

Package Dimensions

TSSOP56-P-0061-0.50A

Unit: mm



Weight: 0.25 g (typ.)

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20070701-EN GENERAL

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